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Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0030			
I _D (A)	248			
Configuration	Single			
Package	PowerPAK SO-8L			

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



Q^D	
GOLI	
N-Channel MOSFET OS	

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	80	V		
Gate-source voltage		V_{GS}	± 20	V		
Continuous drain current	T _C = 25 °C	1	248			
	T _C = 125 °C	I _D	143			
Continuous source current (diode conduction)	Is	248	Α			
Pulsed drain current		I _{DM}	420			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	42			
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	88	mJ		
Maximum power dissipation	T _C = 25 °C	Р	500	W		
	T _C = 125 °C	P_{D}	166	VV		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature) ^b			260	C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount a	R_{thJA}	42	°C/W		
Junction-to-case (drain)		R_{thJC}	0.3	C/VV		

Notes

- a. When mounted on 1" square PCB (FR4 material)
- b. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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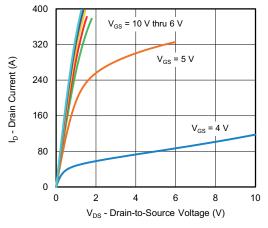
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		80	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.2	2.7	3.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	10		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	250		
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.0025	0.0030	Ω	
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	I _D = 15 A, T _J = 125 °C	-	-	0.0059		
		$V_{GS} = 10 \text{ V}$	I _D = 15 A, T _J = 175 °C	-	-	0.0075	1	
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 10 A	-	82	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	4746	6645	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	814	1140		
Reverse transfer capacitance	C _{rss}			-	51	72		
Total gate charge ^c	Q_g			-	78	117		
Gate-source charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 40 \text{ V}, I_{D} = 10 \text{ A}$	-	18	-	nC	
Gate-drain charge ^c	Q_{gd}			-	16	-		
Gate resistance	R_g		f = 1 MHz		1.0	1.50	Ω	
Turn-on delay time ^c	t _{d(on)}			-	16	20		
Rise time ^c	t _r		$V_{DD} = 40 \text{ V}, \text{ R}_L = 4 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		10	15	ns	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 A$,			39	50		
Fall time ^c	t _f				9	15		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed current ^a	I _{SM}			-	-	420	Α	
Forward voltage	V_{SD}	I _F =	I _F = 15 A, V _{GS} = 0 V		-	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	50	65	ns	
Body diode reverse recovery charge	Q _{rr}			-	71	95	nC	
Reverse recovery fall time	t _a			-	28	44	ns	
Reverse recovery rise time	t _b			-	22	38		
Body diode peak reverse recovery current	I _{RM(REC)}			-	2.4	3.6	Α	

Notes

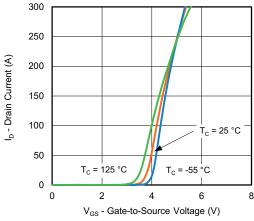
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

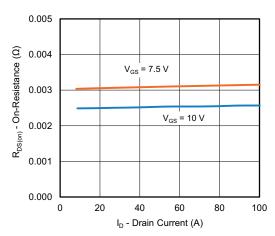




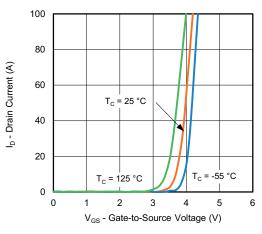
Output Characteristics



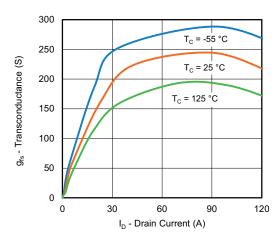
Transfer Characteristics



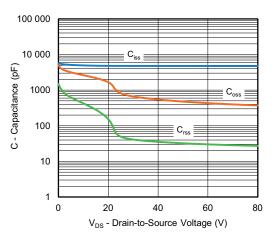
On-Resistance vs. Drain Current



Transfer Characteristics

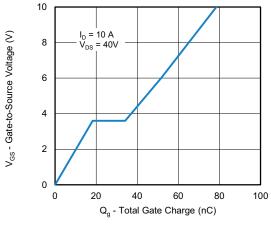


Transconductance

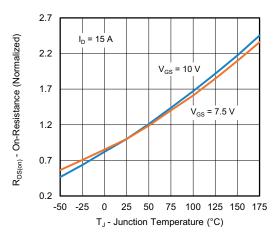


Capacitance

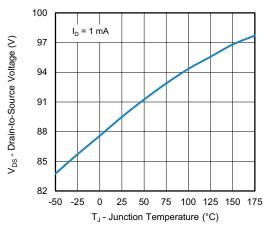




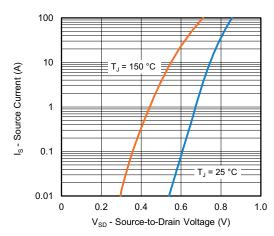




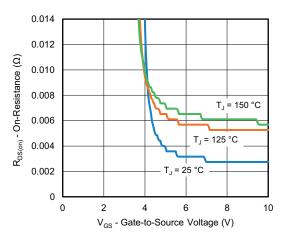
On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature

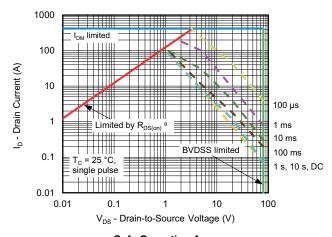


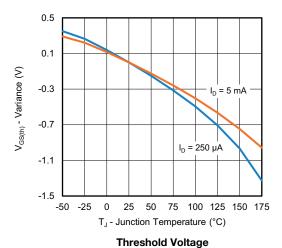
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to Source Voltage





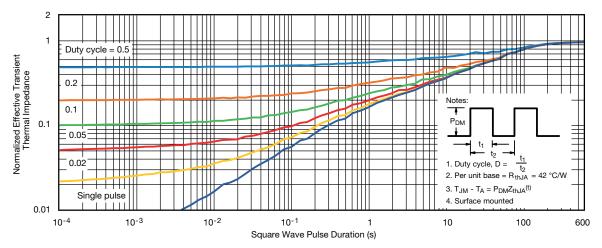


Safe Operating Area

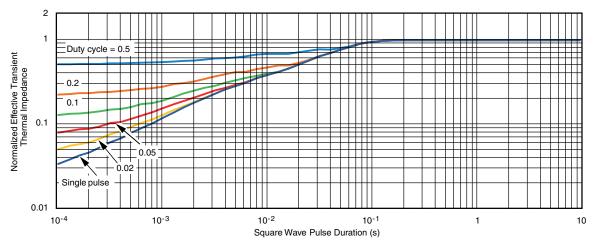
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

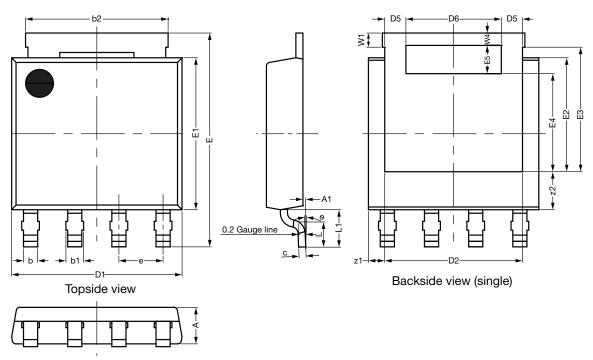
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77297.



PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS			INCHES			
Dilvi.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.00	1.05	1.10	0.039	0.041	0.043		
A1	0.00		0.127	0.000		0.005		
b	0.33	0.41	0.49	0.013	0.016	0.019		
b1	0.43	0.51	0.59	0.017	0.020	0.023		
b2	4.00	4.10	4.20	0.157	0.161	0.165		
С	0.15	0.20	0.25	0.006	0.008	0.010		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D5	0.51	0.61	0.71	0.020	0.024	0.028		
D6	2.64	2.74	2.84	0.104	0.108	0.112		
е		1.27 BSC	•	0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
E3	3.48	3.58	3.68	0.137	0.141	0.145		
E4	2.72	2.82	2.92	0.107	0.111	0.115		
E5	0.71	0.81	0.91	0.028	0.032	0.036		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
W1	0.31	0.41	0.51	0.012	0.016	0.020		
W4	0.31	0.36	0.41	0.012	0.014	0.016		
z1	0.37	0.47	0.57	0.015	0.019	0.022		
z2	0.99	1.09	1.19	0.039	0.043	0.047		
θ	0°		5°	0°		5°		

ECN: C22-1223-Rev. C, 19-Dec-2022

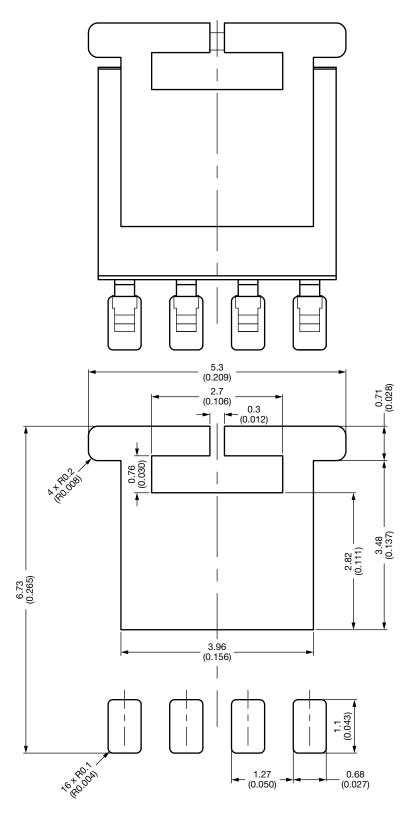
DWG: 6067 **Note**

Millimeter will govern

Revison: 19-Dec-2022 1 Document Number: 76666



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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